

Patent Certificate for Invention

Title of invention: LAYERED GaAs, METHOD OF PREPARING SAME, AND GaAs NANOSHEET EXFOLIATED FROM SAME

Inventors: SHIM, Woo Young
Choi, Sang jin
Hyesoo Kim

Patent No.: ZL 201910420208.1

Filing date: May 20, 2019

Patentee: INDUSTRY-ACADEMIC COOPERATION FOUNDATION, YONSEI UNIVERSITY

Address: Seoul (KR)

Date of patent: January 28, 2022 Patent publication No.: CN 110498445 B

In accordance with the Patent Law, it is found after examination that there is no ground for rejection of the above-identified application, the Patent Office made a decision to grant patent right, issue this patent certificate and register it in the patent register. The patent right took effect from the date of announcement of grant of patent right. The duration of patent right for this patent shall be twenty years, counted from the filing date of the application.

The patent certificate records the legal status when the patent right is granted. The contents to be recorded in the patent register include transfer of the patent right, pledge of the patent right, invalidation of the patent right, termination of the patent right, restoration of the patent right, and change in the name, nationality and address of the patentee, and so on.

The patentee shall pay the annual fees according to the Patent Law and its Implementing Regulations. The annual fees shall be paid in advance within one month before **May 20** of each year. Where the patentee fails to pay the annual fee under the provisions, the patent right shall cease from the expiration date of the previous year.

Applicant and Inventors filed on the filing date:

Applicant: INDUSTRY-ACADEMIC COOPERATION FOUNDATION, YONSEI UNIVERSITY

Inventors: SHIM, Woo Young
Choi, Sang jin
Hyesoo Kim

证书号 第 4907613 号



发明 专利 证书

发明名称：层状 GaAs、其制备方法及由此剥离的 GaAs 纳米片

发明人：沈祐永；崔相珍；金慧修

专利号：ZL 2019 1 0420208.1

专利申请日：2019 年 05 月 20 日

专利权人：延世大学校产学协力团

地址：韩国首尔市

授权公告日：2022 年 01 月 28 日

授权公告号：CN 110498445 B

国家知识产权局依照中华人民共和国专利法进行审查，决定授予专利权，颁发发明专利证书并在专利登记簿上予以登记。专利权自授权公告之日起生效。专利权期限为二十年，自申请日起算。

专利证书记载专利权登记时的法律状况。专利权的转移、质押、无效、终止、恢复和专利权人的姓名或名称、国籍、地址变更等事项记载在专利登记簿上。



局长
申长雨

申长雨



第 1 页 (共 2 页)

其他事项参见续页

证书号 第 4907613 号



专利权人应当依照专利法及其实施细则规定缴纳年费。本专利的年费应当在每年 05 月 20 日前缴纳。未按照规定缴纳年费的，专利权自应当缴纳年费期满之日起终止。

申请日时本专利记载的申请人、发明人信息如下：

申请人：

延世大学校产学协力团

发明人：

沈祐永；崔相珍；金慧修